

FDS6680

Single N-Channel Logic Level PWM Optimized PowerTrench™ MOSFET

General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

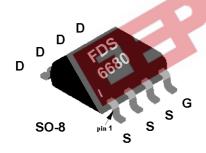
The MOSFET features faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(ON)}}$ specifications.

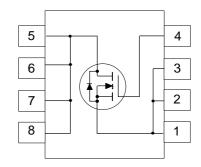
The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- Optimized for use in switching DC/DC converters with PWM controllers.
- Very fast switching.
- Low gate charge (typical Qg = 19 nC).





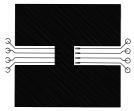


Absolute Maximum Ratings $T_A = 25^{\circ}\text{C}$ unless other wise noted

Symbol	Parameter	FDS6680	Units
V _{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1a)	11.5	А
	- Pulsed	50	
P_{D}	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1	
Γ_{J} , T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
THERMA	CHARACTERISTICS		·
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu A$, Referenced to $25 ^{\circ} C$		23		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ V_{GS} = 0 \text{ V}$			1	μA
		$T_J = 55^{\circ}C$			10	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
ON CHARAC	CTERISTICS (Note 2)	•				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.7	3	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp.Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-5		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 11.5 \text{ A}$		0.0085	0.01	Ω
		T _J =125°C	;	0.014	0.017	
		$V_{GS} = 4.5 \text{ V}, I_D = 9.5 \text{ A}$		0.0125	0.015	
D(ON)	On-State Drain Current	$V_{GS} = 10 \text{ V}, \ V_{DS} = 5 \text{ V}$	50			Α
9 _{FS}	Forward Transconductance	$V_{DS} = 15 \text{ V}, I_{D} = 11.5 \text{ A}$		40		S
DYNAMIC C	CHARACTERISTICS	. 43%	110			
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		2070		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		510		pF
C _{rss}	Reverse Transfer Capacitance			235		pF
SWITCHING	CHARACTERISTICS (Note 2)					
t _{D(on)}	Turn - On Delay Time	$V_{DS} = 15 \text{ V}, I_{D} = 1 \text{ A}$		13	21	ns
ţ,	Turn - On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		10	18	ns
D(off)	Turn - Off Delay Time			36	58	ns
t,	Turn - Off Fall Time			13	23	ns
Q_g	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 11.5 \text{ A},$		19	27	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 5 V		7		nC
Q_{gd}	Gate-Drain Charge			6		nC
DRAIN-SOU	RCE DIODE CHARACTERISTICS AND MAXI	MUM RATINGS				
l _s	Maximum Continuous Drain-Source Diode Forward Current				2.1	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 2.1 \text{ A} \text{ (Note 2)}$			1.2	V

1. R_{gus} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{guc} is guaranteed by design while R_{gcs} is determined by the user's board design.



a. 50°C/W on a 1 in² pad of 2oz copper.





Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

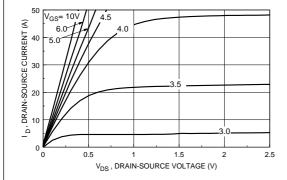


Figure 1. On-Region Characteristics.

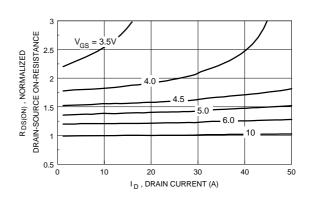


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

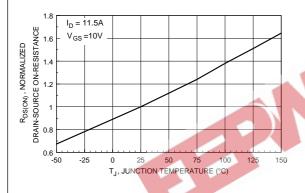


Figure 3. On-Resistance Variation with Temperature.

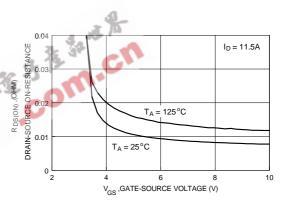


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

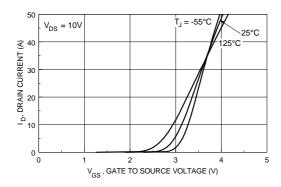


Figure 5. Transfer Characteristics.

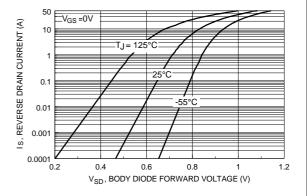
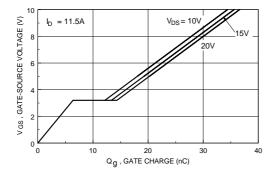


Figure 6. Body Diode Forward Voltage
Variation with Source Current
and Temperature.

Typical Electrical And Thermal Characteristics



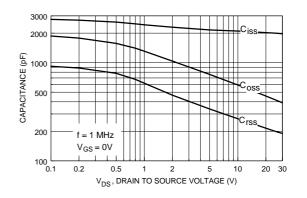
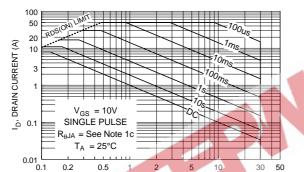


Figure 7. Gate Charge Characteristics.



V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 8. Capacitance Characteristics.

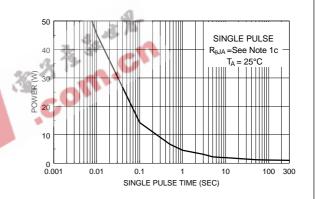


Figure 9. Maximum Safe Operating Area.

0.2

0.5



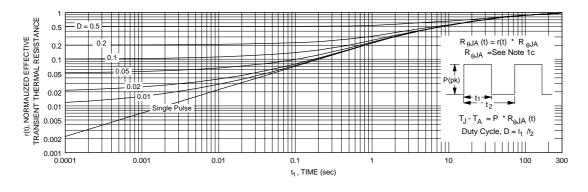
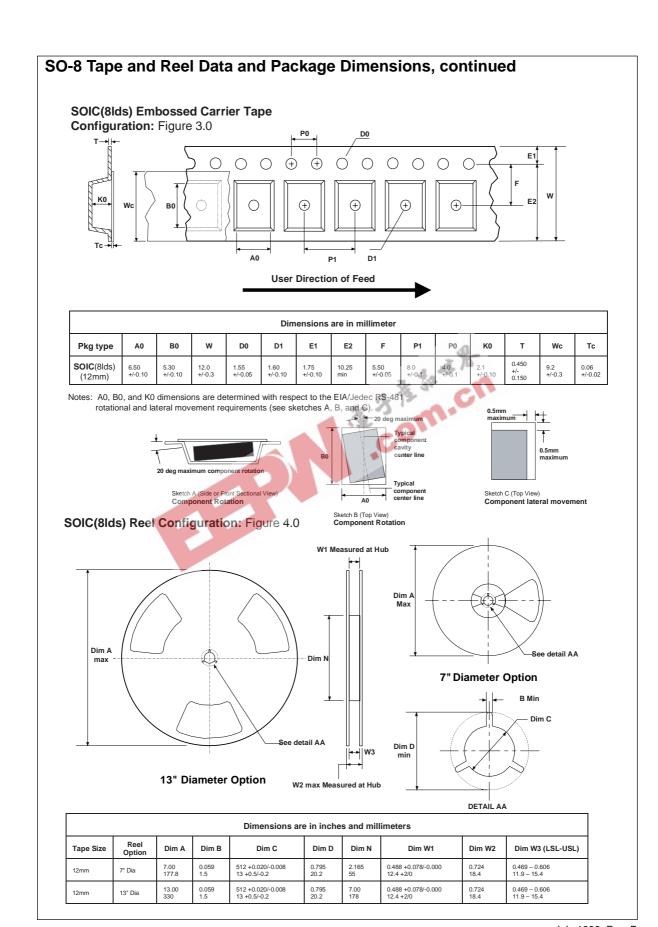


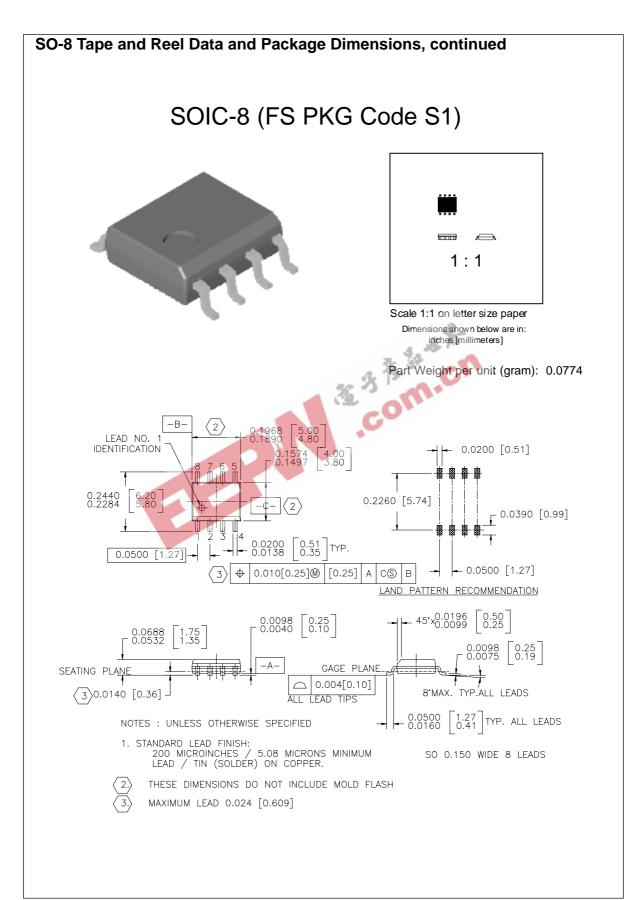
Figure 11. Transient Thermal Response Curve.

30 50

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.







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